



Micro Commercial Components
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MPSA06

Features

- NPN Silicon Epitaxial planar Transistor for switching and amplifier applications
- As complementary type, the PNP transistor is MPSA56
- On special request, this transistor is also manufactured in the pin configuration TO-18

Mechanical Data

- Case: TO-92, Molded Plastic
- Weight: 0.18 grams (Approx.)

Maximum Ratings @ 25°C Unless Otherwise Specified

Characteristic	Symbol	Value	Unit
Collect to Base Voltage	V_{CBO}	80	V
Collect to Emitter Voltage	V_{CEO}	80	V
Emitter to Base Voltage	V_{EBO}	4.0	V
Collect Current	I_C	500	mA
Total Power Dissipation @ $T_A=25^\circ\text{C}$	P_{tot}	625	mW
Total Power Dissipation @ $T_C=25^\circ\text{C}$	P_{tot}	1.5	W
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 to 150	$^\circ\text{C}$

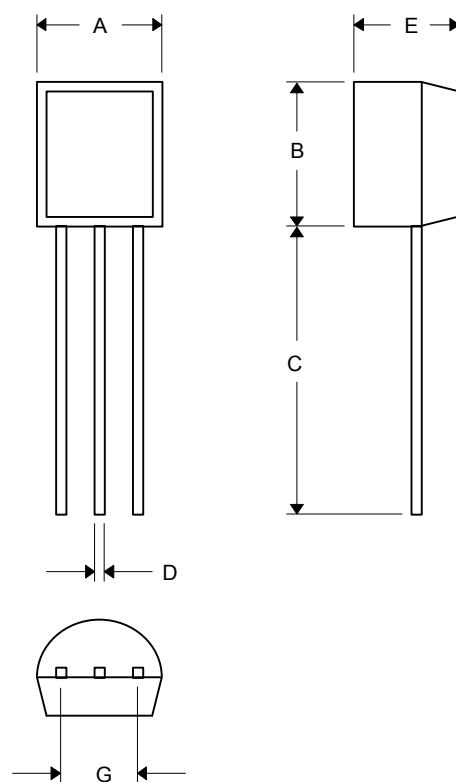
Electrical Characteristics @ 25°C Unless Otherwise Specified

Charateristic	Symbol	Min	Max	Unit	Test Cond.
Collector Cut-off Current	I_{CBO}		100	nA	$V_{CB}=80\text{V}$, $I_E=0$
Collector to Emitter Saturatuion Voltage	$V_{CE(sat)}$		0.25	V	$I_C=100\text{mA}$, $I_B=10\text{mA}$
DC Current Gain	h_{FE}	100 100			$V_{CE}=1\text{V}$, $I_C=10\text{mA}$ $V_{CE}=1\text{V}$, $I_C=100\text{mA}$
Gain Bandwidth Product	f_T	100		MHz	$V_{CE}=2\text{V}$, $I_C=20\text{mA}$, $f=100\text{MHz}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	80		V	$I_C=1\text{mA}$, $I_B=0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	4		V	$I_E=100\mu\text{A}$, $I_C=0$
Base-Emitter ON Voltage	$V_{BE(ON)}$		1.2	V	$I_C=10\text{mA}$, $I_B=1\text{mA}$

Note: Valid provided that leads are kept at ambient temperature.

NPN Small Signal Transistor 625 mW

TO-92



DIMENSIONS					
DIM	INCHES		MM		NOTE
	MIN	MAX	MIN	MAX	
A	.175	.185	4.45	4.70	
B	.175	.185	4.46	4.70	
C	.500	---	12.7	---	
D	.016	.020	0.41	0.63	
E	.135	.145	3.43	3.68	
G	.095	.105	2.42	2.67	